



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
 - 110 mΩ @ V_{GS} = 4.5V
 - 145 m Ω @ V_{GS} = 2.5V
 - 230 m Ω @ V_{GS} = 1.8V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 1, 2 and 3)
- Qualified to AEC-Q101 Standards for High Reliability

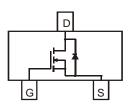
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)





Top View



Top View Internal Schematic

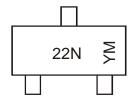
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2230U-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposefully added lead. Halogen and Antimony Free.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Product manufactured with Green Molding Compound and does not contain Halogens or Sb_2O_3 Fire Retardants.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



22N = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	201	1 20	12	2013	2014	2015	2016	2017
Code	U	V	W	X	Υ		Z	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±12	V
Drain Current (Note 5)	I _D	2.0	Α
Pulsed Drain Current (Note 6)	I _{DM}	7	Α

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_{D}	600	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	208	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

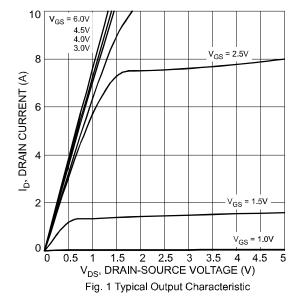
Electrical Characteristics @T_A = 25°C unless otherwise specified

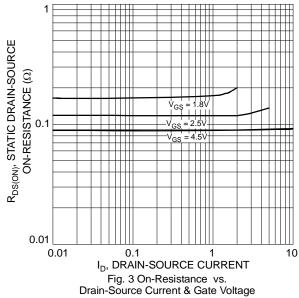
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_		V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}			1	μА	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}			±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	_	1.0	V	$V_{DS} = V_{CS}, I_D = 250 \mu A$
		_	81 113 170	110	mΩ	$V_{GS} = 4.5V, I_D = 2.5A$
Static Drain-Source On-Resistance	R _{DS (ON)}			145		$V_{GS} = 2.5V, I_D = 1.5A$
				230		$V_{GS} = 1.8V, I_D = 1.0A$
Forward Transfer Admittance	Y _{fs}		5		S	$V_{DS} = 5V, I_{D} = 2.4A$
Diode Forward Voltage (Note 7)	V_{SD}		0.8	1.1	V	$V_{GS} = 0V, I_S = 1.05A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}		188	_	pF	
Output Capacitance	Coss		44		pF	$V_{DS} = 10V$, $V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		30	_	pF	I = 1.0IVII IZ
Total Gate Charge	Q_{g}		2.3	_	nC	
Gate-Source Charge	Qgs		0.3		nC	$V_{DS} = 10V, I_D = 11.6A$
Gate-Drain Charge	Q_{gd}	_	0.5		nC	
Turn-On Delay Time	t _{d(on)}	_	8			
Rise Time	t _r	_	3.8	_	ns	$V_{DD} = 10V$, $R_L = 10\Omega$
Turn-Off Delay Time	t _{d(off)}	_	19.6	_	115	$I_D = 1A, V_{GEN} = 4.5V, R_G = 6\Omega$
Fall Time	t _f	_	8.3	_		

Notes:

- 5. Device mounted on FR-4 PCB, or minimum recommended pad layout
- Sepetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.







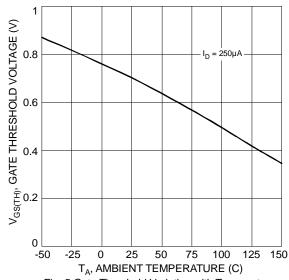
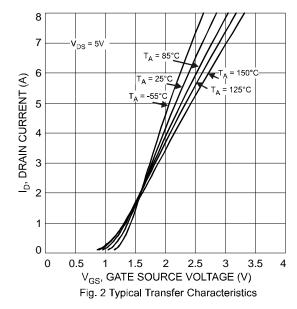


Fig. 5 Gate Threshold Variation with Temperature



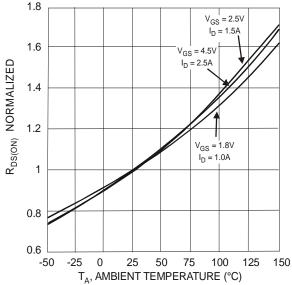
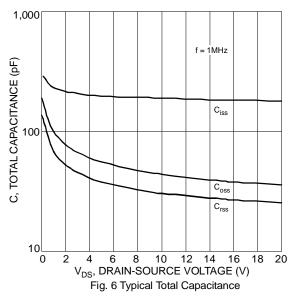
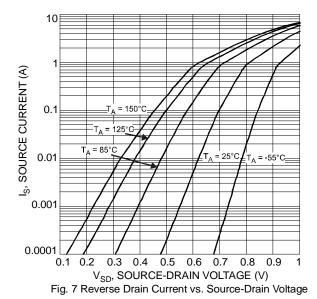
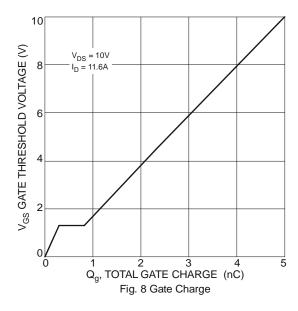


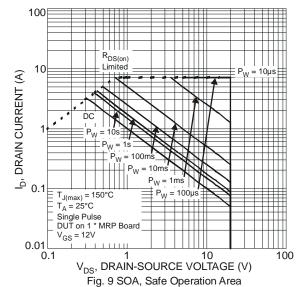
Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



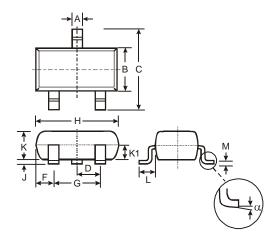








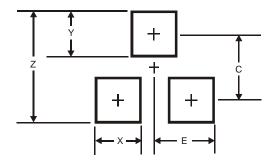
Package Outline Dimensions



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Η	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All Dimensions in mm						



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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